## NSN 5962-01-157-9099

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-157-9099

view Offinite at https://aerobasegroup.com/hist//3302-01-137-3035
Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
0.210 inches
Maximum Power Dissipation Rating:
1.02 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and monolithic and schottky and bipolar and programmable and programmed and positive outputs
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
13 input
Case Outline Source And Designator:
D-3 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.5 volts power source
Time Rating Per Chacteristic:
90.00 nanoseconds propagation delay time, low to high level output and 90.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Rom
Memory Capacity:
Unknown
Special Features:
Alter in accordance w/g.E. Drawing 77a102343p1
Test Data Document:
81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain

environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

## **Terminal Type And Quantity:**

24 printed circuit

## **Specification Data:**

813/0-mil-m-38510/208/usaf/ government specification

## NSN 5962-01-157-9099

Memory Microcircuit - Page 2 of 2



Shelf Life:

N/a

**Unit Of Measure:** 

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Demilitarization:

Yes - demil/mli

Fiig:

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